

US-PAT-NO: 5653892  
DOCUMENT-IDENTIFIER: US 5653892 A  
TITLE: Etching of ceramic materials with an elevated thin film

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Detailed Description Text - DETX (7):

In FIG. 1 a photoresist layer 36 has been patterned by conventional photolithography over an organic layer 38 which covers the BST substrate 40. Organic layer 38 may be any easily removed material having the desired physical characteristics such as Polyimide Release Layer, "PIRL", a trademark of Brewer Science, Inc., or photoresist. Layer 38 is patterned into a grid over the points on the substrate 40 which will become thermal isolation trenches as shown in FIG. 2. Layer 38 may itself be photodefineable, or it may be patterned using a separate mask layer.

US-PAT-NO: 5607600  
DOCUMENT-IDENTIFIER: US 5607600 A  
TITLE: Optical coat reticulation post hybridization

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Detailed Description Text - DETX (11):

A second embodiment of the present invention is shown in FIGS. 5-7. A protective material 64 may be, for example, spun onto the surface of the integrated circuit sensing circuit 48 prior to bonding infrared sensing array 46 and sensing integrated circuit structure 48 together, as shown in FIG. 5. The protective material 64 is preferably an organic coating comprising photoresist and PIRL (polyimide release layer). After the thermal isolation slots 62 have been etched, the protective material 64 may be removed, for example, as a gas by ashing in a plasma reactor. Preferably, the protective material 64 is removed entirely, as shown in FIG. 6.

US-PAT-NO: 6307721  
DOCUMENT-IDENTIFIER: US 6307721 B1  
TITLE: Thin read gap magnetoresistive (MR)  
sensor element and  
method for fabrication thereof

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Detailed Description Text - DETX (11):

There is also shown in FIG. 1 the presence of a first lift off stencil 16 formed upon the patterned first magnetoresistive (MR) layer 14. The first lift off stencil 16 comprises a patterned first release layer 16a formed upon the patterned first magnetoresistive (MR) layer 14 and a patterned first photoresist layer 16b formed symmetrically overhanging the patterned first release layer 16a. While any of several release materials may be employed in forming the patterned first release layer 16a, including but not limited to organic polymer release materials such as but not limited to polysulfone organic polymer release materials and polyimide organic polymer release materials, for the preferred embodiments of the present invention the patterned first release layer 16a is preferably formed of a PMGI organic polymer release material which is an organic polymer photoresist material. Preferably, the patterned first release layer 16a is formed to a thickness of from about 500 to about 10000 angstroms upon the patterned first magnetoresistive (MR) layer 14. Similarly, although any of several photoresist materials may be employed for forming the patterned first photoresist layer 16b, including but not limited to photoresist materials selected from the general groups of